

# (12) United States Patent

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(54)	SEMICONDUCTOR DEVICE HAVING A
	FERROELECTRIC TFT AND A DUMMY
	ELEMENT

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257/532, 213, 295

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## 57) ABSTRACT

The present invention provides a semiconductor device including a semiconductor element and a dummy semiconductor element adjacent to the semiconductor element. When the semiconductor element is a capacitor element including a bottom electrode, a top electrode and a dielectric layer between the electrodes, a dummy capacitor element also has dummy electrodes and a dummy dielectric layer between the dummy electrodes. The dummy electrode is located so that a space between the top electrode of the capacitor element ad the dummy top electrode is in a predetermined range (e.g.  $0.3~\mu m$  to  $14~\mu m$ ). The dummy capacitor element prevents the capacitor dielectric layer from degrading since the collision of the etching ions with the capacitor dielectric layer in a dry etching process is suppressed.

## 5 Claims, 21 Drawing Sheets

